

| | Type | Hits | Search Text | DBs |
|---|------|---------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------|
| 1 | BRS | 1208348 | sio? or "sio.sub.2" or oxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 2 | BRS | 1854 | ("L" or L near (shap\$4 or form\$4)) near4 spacer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 3 | BRS | 153605 | mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 4 | BRS | 4638 | (sio? or "sio.sub.2" or oxide) near8 (liner or conformal\$4) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 5 | BRS | 14 | ((("L" or L near (shap\$4 or form\$4)) near4 spacer) same ((sio? or "sio.sub.2" or oxide) near8 (liner or conformal\$4)) and (mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 6 | BRS | 9006 | (second! or another or additional\$4 or further) near4 (inplant or implant or implanting or implanting) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 7 | BRS | 39 | ((("L" or L near (shap\$4 or form\$4)) near4 spacer) and ((second! or another or additional\$4 or further) near4 (inplant or implant or implanting or implanting))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |

| | Type | Hits | Search T xt | DBs |
|----|------|--------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------|
| 8 | BRS | 37 | ((("L" or L near (shap\$4 or form\$4)) near4 spacer) and ((second! or another or additional\$4 or further) near4 (implant or implant or implanting or implanting))) not (((("L" or L near (shap\$4 or form\$4)) near4 spacer) same ((sio? or "sio.sub.2" or oxide) near8 (liner or conformal\$4)) and (mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 9 | BRS | 37 | ((("L" or L near (shap\$4 or form\$4)) near4 spacer) and ((second! or another or additional\$4 or further) near4 (implant or implant or implanting or implanting))) not (((("L" or L near (shap\$4 or form\$4)) near4 spacer) same ((sio? or "sio.sub.2" or oxide) near8 (liner or conformal\$4)) and (mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet))) and | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 10 | BRS | 153605 | mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 11 | BRS | 132073 | (source or drain) same (boron or B or "bf.sub.2" or indium) same (arsenic or as or phosphorus or p or antimony or sb) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 12 | BRS | 363 | (source or drain) near8 (boron or B or "bf.sub.2" or indium) near8 (arsenic or as or phosphorus or p or antimony or sb) near8 (concentration or dosage) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 13 | BRS | 1097 | (source or drain) near8 (boron or B or "bf.sub.2" or indium) near8 (concentration or dosage) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |

| | Type | Hits | S arch Text | DBs |
|----|------|------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------|
| 14 | BRS | 4627 | (source or drain) near8 (arsenic or as or phosphorus or p or antimony or sb) near8 (concentration or dosage) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 15 | BRS | 409 | ((source or drain) near8 (boron or B or "bf.sub.2" or indium) near8 (concentration or dosage)) and ((source or drain) near8 (arsenic or as or phosphorus or p or antimony or sb) near8 (concentration or dosage)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 16 | BRS | 74 | (source or drain) near8 (boron or B or "bf.sub.2" or indium) near8 (concentration or dosage) near8 (kev or energy) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 17 | BRS | 238 | (source or drain) near8 (arsenic or as or phosphorus or p or antimony or sb) near8 (concentration or dosage) near8 (kev or energy) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 18 | BRS | 18 | ((source or drain) near8 (boron or B or "bf.sub.2" or indium) near8 (concentration or dosage) near8 (kev or energy)) and ((source or drain) near8 (arsenic or as or phosphorus or p or antimony or sb) near8 (concentration or dosage) near8 (kev or energy)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 19 | IS&R | 183 | ((438/184) or (438/185) or (438/181)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |